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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	624
Number of Logic Elements/Cells	4992
Total RAM Bits	24576
Number of I/O	274
Number of Gates	158000
Voltage - Supply	3V ~ 3.6V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	356-LBGA
Supplier Device Package	356-BGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k100abc356-3

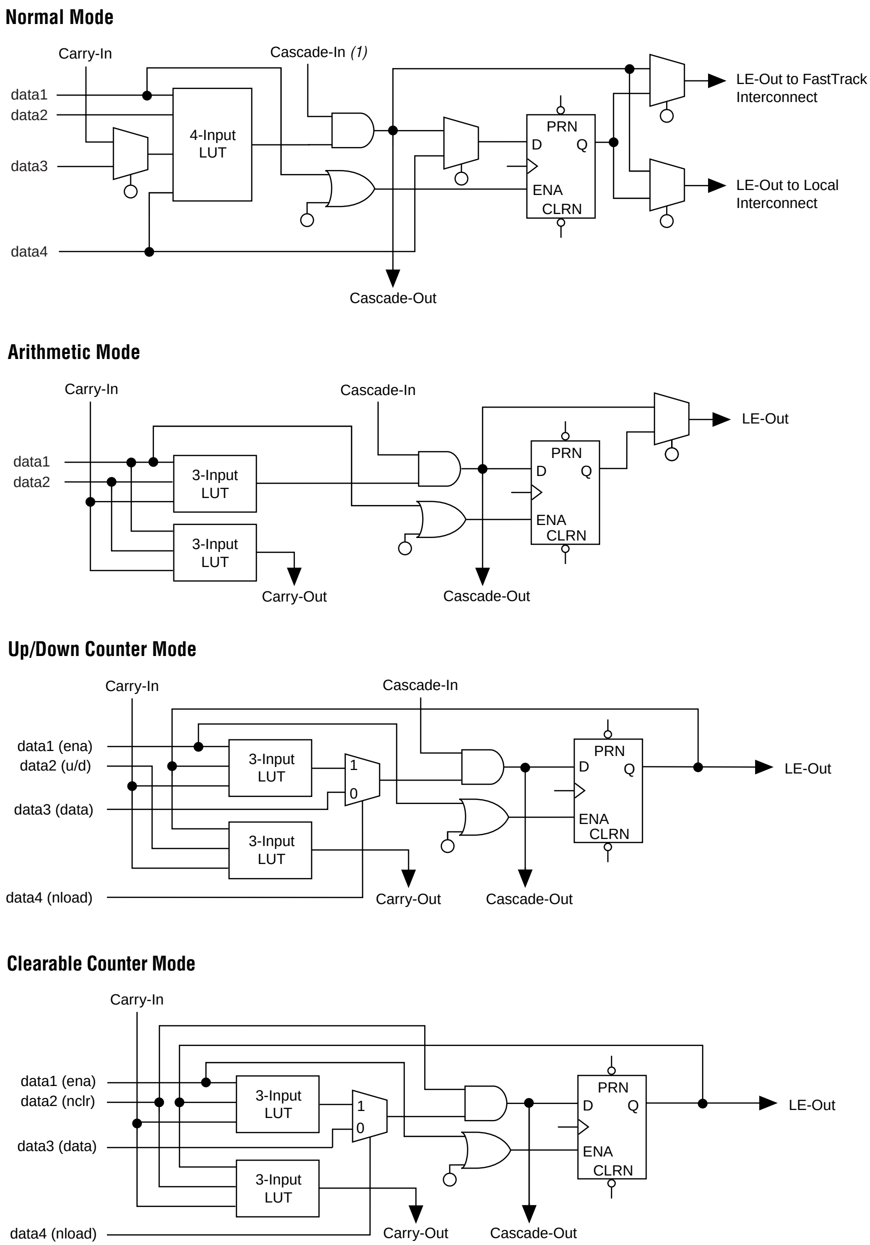
Table 4. FLEX 10K Package Options & I/O Pin Count Note (1)

Device	84-Pin PLCC	100-Pin TQFP	144-Pin TQFP	208-Pin PQFP RQFP	240-Pin PQFP RQFP
EPF10K10	59		102	134	
EPF10K10A		66	102	134	
EPF10K20			102	147	189
EPF10K30				147	189
EPF10K30A			102	147	189
EPF10K40				147	189
EPF10K50					189
EPF10K50V					189
EPF10K70					189
EPF10K100					
EPF10K100A					189
EPF10K130V					
EPF10K250A					

Table 5. FLEX 10K Package Options & I/O Pin Count (Continued) Note (1)

Device	503-Pin PGA	599-Pin PGA	256-Pin FineLine BGA	356-Pin BGA	484-Pin FineLine BGA	600-Pin BGA	403-Pin PGA
EPF10K10							
EPF10K10A			150		150 *(2)*		
EPF10K20							
EPF10K30				246			
EPF10K30A			191	246	246		
EPF10K40							
EPF10K50				274			310
EPF10K50V				274			
EPF10K70	358						
EPF10K100	406						
EPF10K100A				274	369	406	
EPF10K130V		470				470	
EPF10K250A		470				470	

Figure 9. FLEX 10K LE Operating Modes



Note:

(1) Packed registers cannot be used with the cascade chain.

FastTrack Interconnect

In the FLEX 10K architecture, connections between LEs and device I/O pins are provided by the FastTrack Interconnect, which is a series of continuous horizontal and vertical routing channels that traverse the device. This global routing structure provides predictable performance, even in complex designs. In contrast, the segmented routing in FPGAs requires switch matrices to connect a variable number of routing paths, increasing the delays between logic resources and reducing performance.

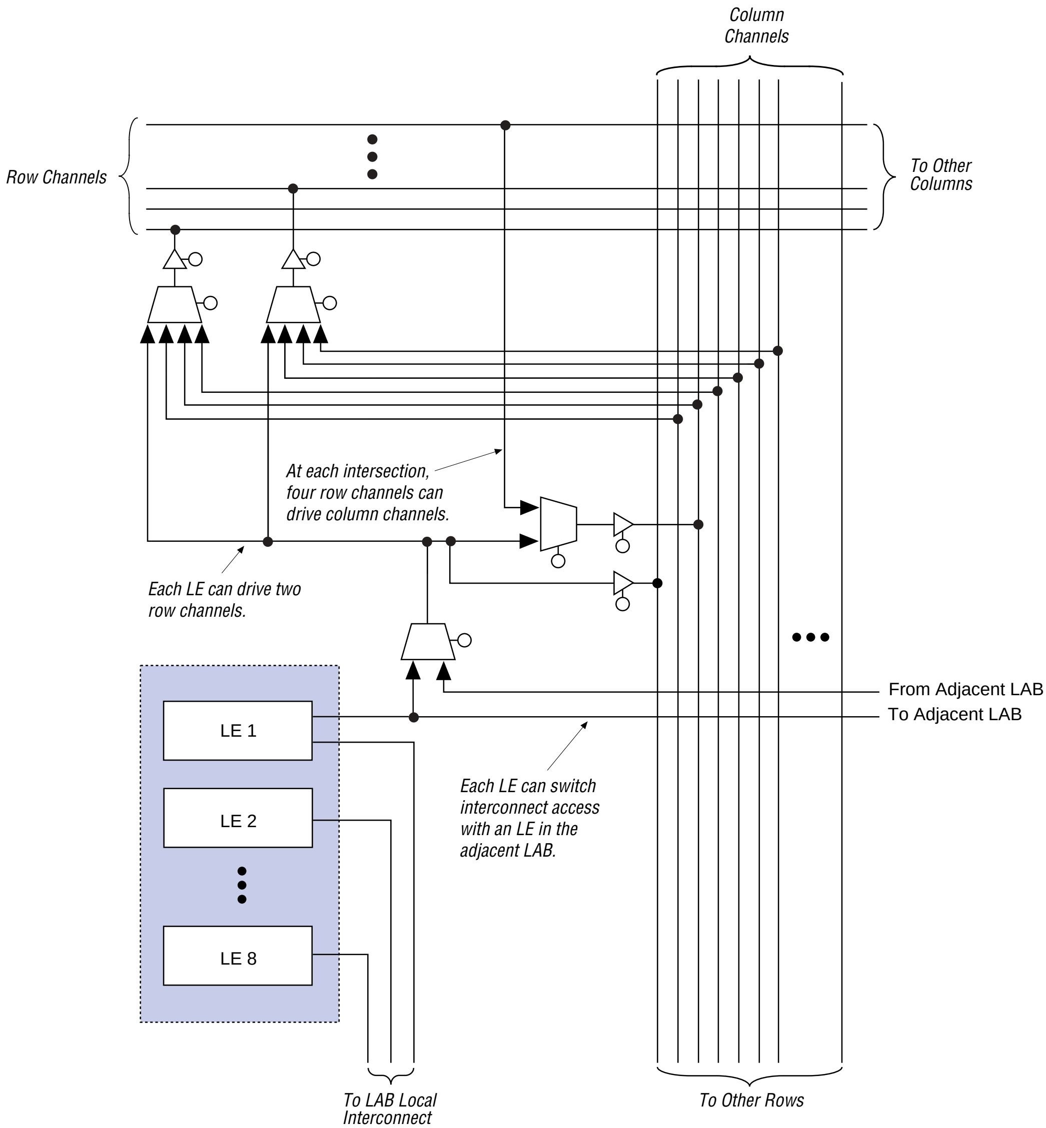
The FastTrack Interconnect consists of row and column interconnect channels that span the entire device. Each row of LABs is served by a dedicated row interconnect. The row interconnect can drive I/O pins and feed other LABs in the device. The column interconnect routes signals between rows and can drive I/O pins.

A row channel can be driven by an LE or by one of three column channels. These four signals feed dual 4-to-1 multiplexers that connect to two specific row channels. These multiplexers, which are connected to each LE, allow column channels to drive row channels even when all eight LEs in an LAB drive the row interconnect.

Each column of LABs is served by a dedicated column interconnect. The column interconnect can then drive I/O pins or another row's interconnect to route the signals to other LABs in the device. A signal from the column interconnect, which can be either the output of an LE or an input from an I/O pin, must be routed to the row interconnect before it can enter an LAB or EAB. Each row channel that is driven by an IOE or EAB can drive one specific column channel.

Access to row and column channels can be switched between LEs in adjacent pairs of LABs. For example, an LE in one LAB can drive the row and column channels normally driven by a particular LE in the adjacent LAB in the same row, and vice versa. This routing flexibility enables routing resources to be used more efficiently. See Figure 11.

Figure 11. LAB Connections to Row & Column Interconnect



I/O Element

An I/O element (IOE) contains a bidirectional I/O buffer and a register that can be used either as an input register for external data that requires a fast setup time, or as an output register for data that requires fast clock-to-output performance. In some cases, using an LE register for an input register will result in a faster setup time than using an IOE register. IOEs can be used as input, output, or bidirectional pins. For bidirectional registered I/O implementation, the output register should be in the IOE and, the data input and output enable register should be LE registers placed adjacent to the bidirectional pin. The Compiler uses the programmable inversion option to invert signals from the row and column interconnect automatically where appropriate. Figure 13 shows the bidirectional I/O registers.

Figure 13. Bidirectional I/O Registers

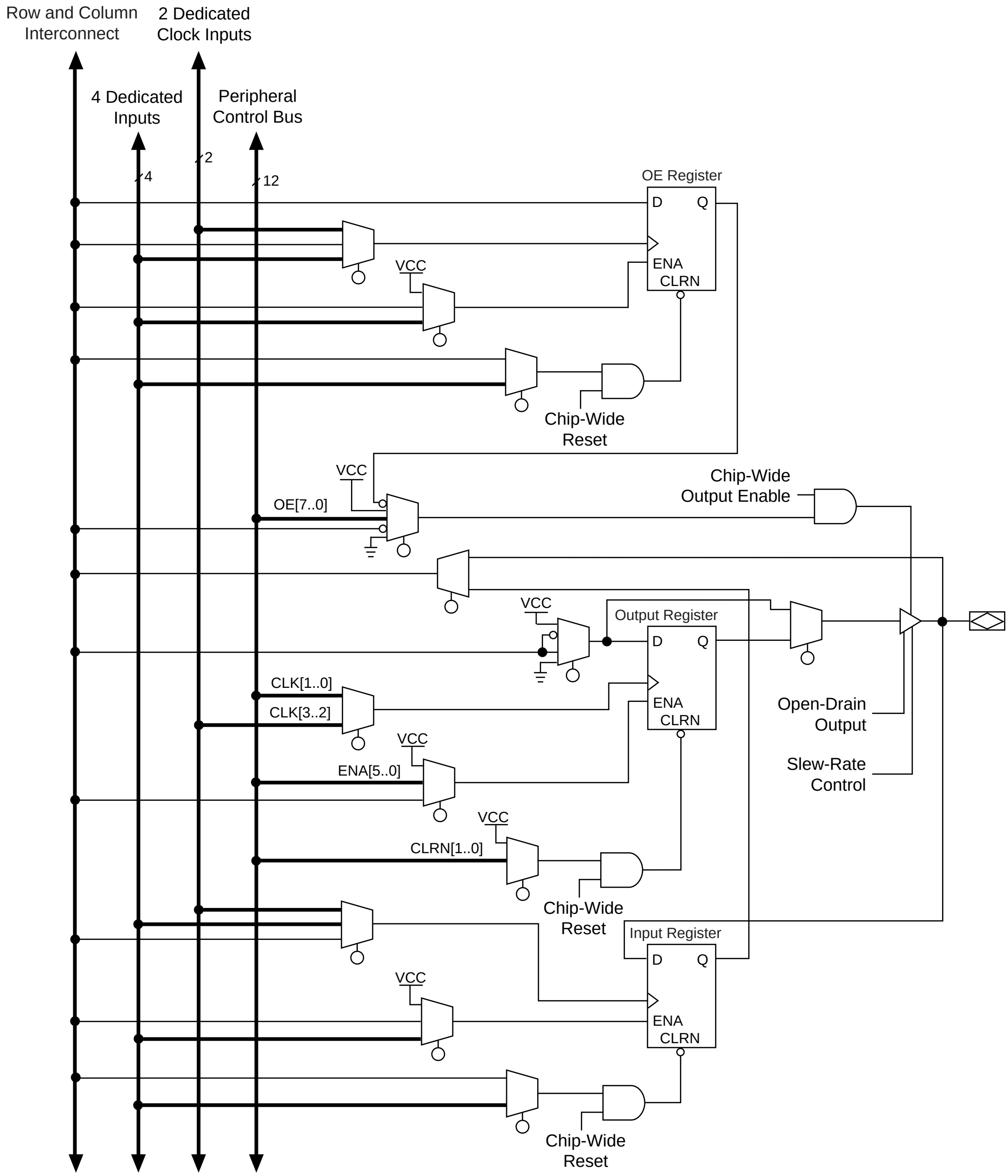


Table 19. FLEX 10K 5.0-V Device DC Operating Conditions *Notes (5), (6)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		2.0		V_{CCINT} + 0.5	V
V_{IL}	Low-level input voltage		–0.5		0.8	V
V_{OH}	5.0-V high-level TTL output voltage	I_{OH} = –4 mA DC, V_{CCIO} = 4.75 V *(7)*	2.4			V
	3.3-V high-level TTL output voltage	I_{OH} = –4 mA DC, V_{CCIO} = 3.00 V *(7)*	2.4			V
	3.3-V high-level CMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(7)*	V_{CCIO} – 0.2			V
V_{OL}	5.0-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 4.75 V *(8)*			0.45	V
	3.3-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(8)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(8)*			0.2	V
I_I	Input pin leakage current	V_I = V_{CC} or ground *(9)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = V_{CC} or ground *(9)*	–40		40	µA
I_{CC0}	V_{CC} supply current (standby)	V_I = ground, no load		0.5	10	mA

Table 20. 5.0-V Device Capacitance of EPF10K10, EPF10K20 & EPF10K30 Devices *Note (10)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

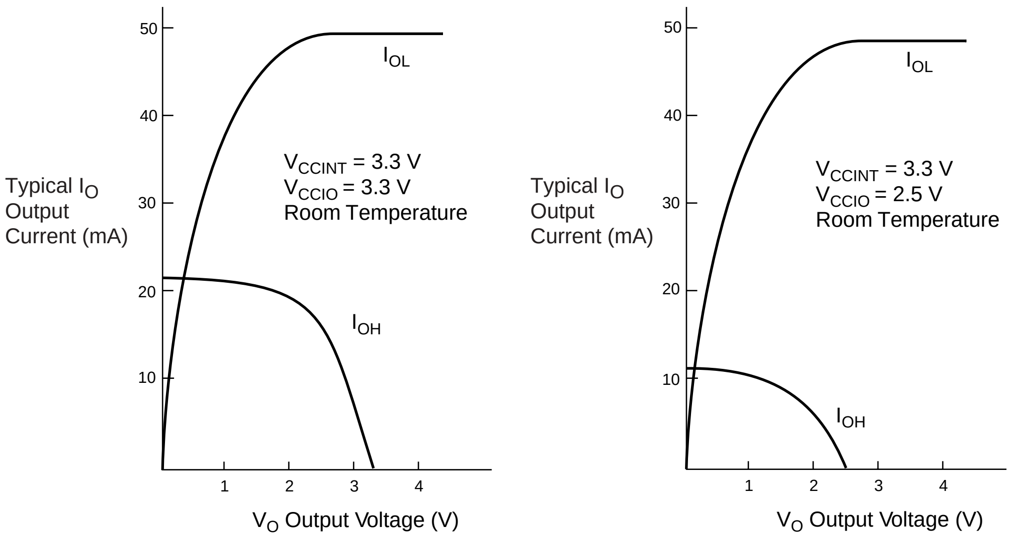
Table 21. 5.0-V Device Capacitance of EPF10K40, EPF10K50, EPF10K70 & EPF10K100 Devices *Note (10)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		10	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		15	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		10	pF

Table 27. FLEX 10KA 3.3-V Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	(3), (4)	3.00 (3.00)	3.60 (3.60)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	(3), (4)	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	(3), (4)	2.30 (2.30)	2.70 (2.70)	V
V_I	Input voltage	(5)	–0.5	5.75	V
V_O	Output voltage		0	V_{CCIO}	V
T_A	Ambient temperature	For commercial use	0	70	° C
		For industrial use	–40	85	° C
T_J	Operating temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Figure 23. Output Drive Characteristics for EPF10K250A Device



Timing Model

The continuous, high-performance FastTrack Interconnect routing resources ensure predictable performance and accurate simulation and timing analysis. This predictable performance contrasts with that of FPGAs, which use a segmented connection scheme and therefore have unpredictable performance.

Device performance can be estimated by following the signal path from a source, through the interconnect, to the destination. For example, the registered performance between two LEs on the same row can be calculated by adding the following parameters:

- LE register clock-to-output delay (t_{CO})
- Interconnect delay ($t_{SAMEROW}$)
- LE look-up table delay (t_{LUT})
- LE register setup time (t_{SU})

The routing delay depends on the placement of the source and destination LEs. A more complex registered path may involve multiple combinatorial LEs between the source and destination LEs.

Table 34. EAB Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
$t_{EABDATA1}$	Data or address delay to EAB for combinatorial input	
$t_{EABDATA2}$	Data or address delay to EAB for registered input	
t_{EABWE1}	Write enable delay to EAB for combinatorial input	
t_{EABWE2}	Write enable delay to EAB for registered input	
t_{EABCLK}	EAB register clock delay	
t_{EABCO}	EAB register clock-to-output delay	
$t_{EABBYPASS}$	Bypass register delay	
t_{EABSU}	EAB register setup time before clock	
t_{EABH}	EAB register hold time after clock	
t_{AA}	Address access delay	
t_{WP}	Write pulse width	
t_{WDSU}	Data setup time before falling edge of write pulse	*(5)*
t_{WDH}	Data hold time after falling edge of write pulse	*(5)*
t_{WASU}	Address setup time before rising edge of write pulse	*(5)*
t_{WAH}	Address hold time after falling edge of write pulse	*(5)*
t_{WO}	Write enable to data output valid delay	
t_{DD}	Data-in to data-out valid delay	
t_{EABOUT}	Data-out delay	
t_{EABCH}	Clock high time	
t_{EABCL}	Clock low time	

Table 35. EAB Timing Macroparameters *Notes (1), (6)*		
Symbol	**Parameter**	**Conditions**
t_{EABAA}	EAB address access delay	
$t_{EABRCCOMB}$	EAB asynchronous read cycle time	
$t_{EABRCREG}$	EAB synchronous read cycle time	
t_{EABWP}	EAB write pulse width	
$t_{EABWCCOMB}$	EAB asynchronous write cycle time	
$t_{EABWCREG}$	EAB synchronous write cycle time	
t_{EABDD}	EAB data-in to data-out valid delay	
$t_{EABDATACO}$	EAB clock-to-output delay when using output registers	
$t_{EABDATASU}$	EAB data/address setup time before clock when using input register	
$t_{EABDATAH}$	EAB data/address hold time after clock when using input register	
$t_{EABWESU}$	EAB WE setup time before clock when using input register	
t_{EABWEH}	EAB WE hold time after clock when using input register	
$t_{EABWDSU}$	EAB data setup time before falling edge of write pulse when not using input registers	
t_{EABWDH}	EAB data hold time after falling edge of write pulse when not using input registers	
$t_{EABWASU}$	EAB address setup time before rising edge of write pulse when not using input registers	
t_{EABWAH}	EAB address hold time after falling edge of write pulse when not using input registers	
t_{EABWO}	EAB write enable to data output valid delay	

Figure 30. EAB Synchronous Timing Waveforms

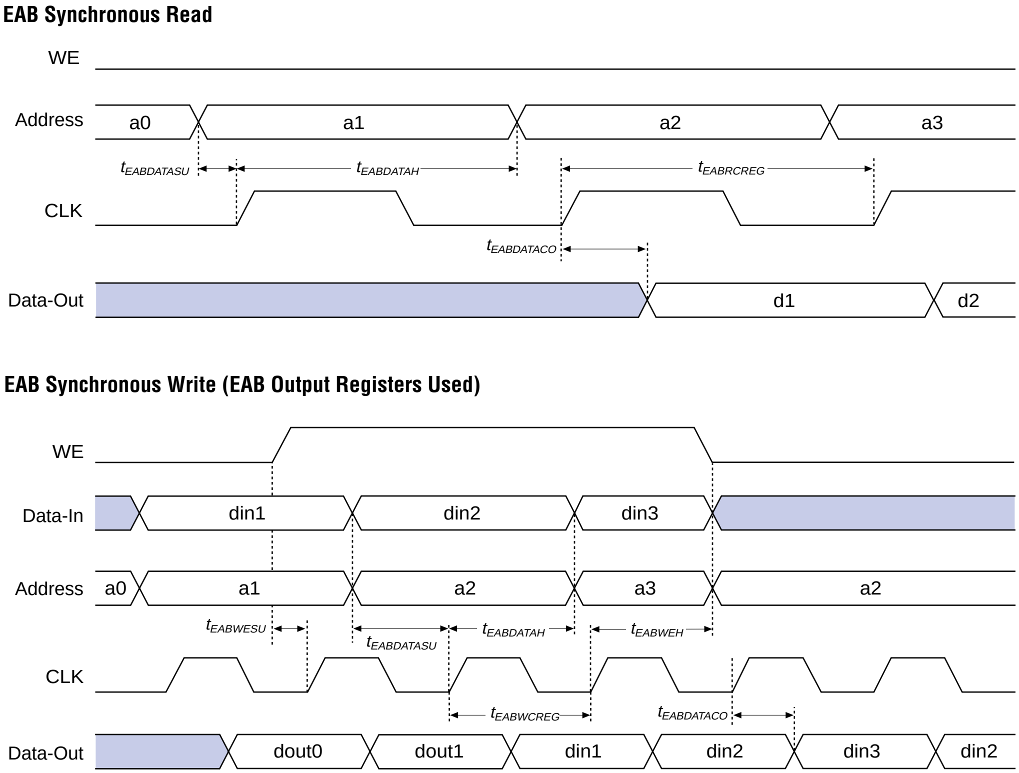


Table 40. EPF10K10 & EPF10K20 Device IOE Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{IOD}		1.3		1.6	ns
t_{IOC}		0.5		0.7	ns
t_{IOCO}		0.2		0.2	ns
t_{IOCOMB}		0.0		0.0	ns
t_{IOSU}	2.8		3.2		ns
t_{IOH}	1.0		1.2		ns
t_{IOCLR}		1.0		1.2	ns
t_{OD1}		2.6		3.5	ns
t_{OD2}		4.9		6.4	ns
t_{OD3}		6.3		8.2	ns
t_{XZ}		4.5		5.4	ns
t_{ZX1}		4.5		5.4	ns
t_{ZX2}		6.8		8.3	ns
t_{ZX3}		8.2		10.1	ns
t_{INREG}		6.0		7.5	ns
t_{IOFD}		3.1		3.5	ns
t_{INCOMB}		3.1		3.5	ns

Table 41. EPF10K10 & EPF10K20 Device EAB Internal Microparameters *Note (1)*					
Symbol	**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	
$t_{EABDATA1}$		1.5		1.9	ns
$t_{EABDATA2}$		4.8		6.0	ns
t_{EABWE1}		1.0		1.2	ns
t_{EABWE2}		5.0		6.2	ns
t_{EABCLK}		1.0		2.2	ns
t_{EABCO}		0.5		0.6	ns
$t_{EABBYPASS}$		1.5		1.9	ns
t_{EABSU}	1.5		1.8		ns
t_{EABH}	2.0		2.5		ns
t_{AA}		8.7		10.7	ns
t_{WP}	5.8		7.2		ns
t_{WDSU}	1.6		2.0		ns
t_{WDH}	0.3		0.4		ns
t_{WASU}	0.5		0.6		ns
t_{WAH}	1.0		1.2		ns
t_{WO}		5.0		6.2	ns
t_{DD}		5.0		6.2	ns
t_{EABOUT}		0.5		0.6	ns
t_{EABCH}	4.0		4.0		ns
t_{EABCL}	5.8		7.2		ns

Table 51. EPF10K30, EPF10K40 & EPF10K50 Device EAB Internal Timing Macroparameters *Note (1)*					
Symbol	**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	
t_{EABAA}		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		17.0		ns
$t_{EABRCREG}$	9.7		11.9		ns
t_{EABWP}	5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		9.0		ns
$t_{EABWCREG}$	13.0		16.0		ns
t_{EABDD}		10.0		12.5	ns
$t_{EABDATACO}$		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		ns
$t_{EABWESU}$	5.5		5.8		ns
t_{EABWEH}	0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.8		ns
t_{EABWDH}	0.0		0.0		ns
$t_{EABWASU}$	2.1		2.7		ns
t_{EABWAH}	0.0		0.0		ns
t_{EABWO}		9.5		11.8	ns

Table 60. EPF10K70 Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		12.1		13.7		17.0	ns
$t_{EABRCCOMB}$	12.1		13.7		17.0		ns
$t_{EABRCREG}$	8.6		9.7		11.9		ns
t_{EABWP}	5.2		5.8		7.2		ns
$t_{EABWCCOMB}$	6.5		7.3		9.0		ns
$t_{EABWCREG}$	11.6		13.0		16.0		ns
t_{EABDD}		8.8		10.0		12.5	ns
$t_{EABDATACO}$		1.7		2.0		3.4	ns
$t_{EABDATASU}$	4.7		5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	4.9		5.5		5.8		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.8		2.1		2.7		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	4.1		4.7		5.8		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		8.4		9.5		11.8	ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 64 through 70 show EPF10K100 device internal and external timing parameters.

Table 64. EPF10K100 Device LE Timing Microparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.5		1.5		2.0	ns
t_{CLUT}		0.4		0.4		0.5	ns
t_{RLUT}		1.6		1.6		2.0	ns
t_{PACKED}		0.9		0.9		1.3	ns
t_{EN}		0.9		0.9		1.2	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		1.1		1.1		1.4	ns
t_{CGENR}		1.2		1.2		1.5	ns
t_{CASC}		1.1		1.1		1.3	ns
t_{C}		0.8		0.8		1.0	ns
t_{CO}		1.0		1.0		1.4	ns
t_{COMB}		0.5		0.5		0.7	ns
t_{SU}	2.1		2.1		2.6		ns
t_{H}	2.3		2.3		3.1		ns
t_{PRE}		1.0		1.0		1.4	ns
t_{CLR}		1.0		1.0		1.4	ns
t_{CH}	4.0		4.0		4.0		ns
t_{CL}	4.0		4.0		4.0		ns

Table 100. EPF10K100A Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		2.5		2.9		3.4	ns
t_{IOC}		0.3		0.3		0.4	ns
t_{IOCO}		0.2		0.2		0.3	ns
t_{IOCOMB}		0.5		0.6		0.7	ns
t_{IOSU}	1.3		1.7		1.8		ns
t_{IOH}	0.2		0.2		0.3		ns
t_{IOCLR}		1.0		1.2		1.4	ns
t_{OD1}		2.2		2.6		3.0	ns
t_{OD2}		4.5		5.3		6.1	ns
t_{OD3}		6.8		7.9		9.3	ns
t_{XZ}		2.7		3.1		3.7	ns
t_{ZX1}		2.7		3.1		3.7	ns
t_{ZX2}		5.0		5.8		6.8	ns
t_{ZX3}		7.3		8.4		10.0	ns
t_{INREG}		5.3		6.1		7.2	ns
t_{IOFD}		4.7		5.5		6.4	ns
t_{INCOMB}		4.7		5.5		6.4	ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 106 through 112 show EPF10K250A device internal and external timing parameters.

Table 106. EPF10K250A Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.9		1.0		1.4	ns
t_{CLUT}		1.2		1.3		1.6	ns
t_{RLUT}		2.0		2.3		2.7	ns
t_{PACKED}		0.4		0.4		0.5	ns
t_{EN}		1.4		1.6		1.9	ns
t_{CICO}		0.2		0.3		0.3	ns
t_{CGEN}		0.4		0.6		0.6	ns
t_{CGENR}		0.8		1.0		1.1	ns
t_{CASC}		0.7		0.8		1.0	ns
t_{C}		1.2		1.3		1.6	ns
t_{CO}		0.6		0.7		0.9	ns
t_{COMB}		0.5		0.6		0.7	ns
t_{SU}	1.2		1.4		1.7		ns
t_{H}	1.2		1.3		1.6		ns
t_{PRE}		0.7		0.8		0.9	ns
t_{CLR}		0.7		0.8		0.9	ns
t_{CH}	2.5		3.0		3.5		ns
t_{CL}	2.5		3.0		3.5		ns

Table 113. ClockLock & ClockBoost Parameters (Part 2 of 2)

Symbol	Parameter	Min	Typ	Max	Unit
$f_{CLKDEV1}$	Input deviation from user specification in MAX+PLUS II (ClockBoost clock multiplication factor equals 1) *(1)*			±1	MHz
$f_{CLKDEV2}$	Input deviation from user specification in MAX+PLUS II (ClockBoost clock multiplication factor equals 2) *(1)*			±0.5	MHz
$t_{INCLKSTB}$	Input clock stability (measured between adjacent clocks)			100	ps
t_{LOCK}	Time required for ClockLock or ClockBoost to acquire lock *(2)*			10	µs
t_{JITTER}	Jitter on ClockLock or ClockBoost-generated clock *(3)*			1	ns
$t_{OUTDUTY}$	Duty cycle for ClockLock or ClockBoost-generated clock	40	50	60	%

Notes:

(1) To implement the ClockLock and ClockBoost circuitry with the MAX+PLUS II software, designers must specify the input frequency. The MAX+PLUS II software tunes the PLL in the ClockLock and ClockBoost circuitry to this frequency. The f_{CLKDEV} parameter specifies how much the incoming clock can differ from the specified frequency during device operation. Simulation does not reflect this parameter.

(2) During device configuration, the ClockLock and ClockBoost circuitry is configured before the rest of the device. If the incoming clock is supplied during configuration, the ClockLock and ClockBoost circuitry locks during configuration, because the t_{LOCK} value is less than the time required for configuration.

(3) The t_{JITTER} specification is measured under long-term observation.

Power Consumption

The supply power (P) for FLEX 10K devices can be calculated with the following equation:

$$P = P_{INT} + P_{IO} = (I_{CCSTANDBY} + I_{CCACTIVE}) \times V_{CC} + P_{IO}$$

Typical $I_{CCSTANDBY}$ values are shown as I_{CC0} in the FLEX 10K device DC operating conditions tables on pages 46, 49, and 52 of this data sheet. The $I_{CCACTIVE}$ value depends on the switching frequency and the application logic. This value is calculated based on the amount of current that each LE typically consumes. The P_{IO} value, which depends on the device output load characteristics and switching frequency, can be calculated using the guidelines given in *Application Note 74 (Evaluating Power for Altera Devices)*.

Compared to the rest of the device, the embedded array consumes a negligible amount of power. Therefore, the embedded array can be ignored when calculating supply current.

The $I_{CCACTIVE}$ value is calculated with the following equation:

$$I_{CCACTIVE} = K \times \mathbf{f_{MAX}} \times N \times \mathbf{tog_{LC}} \times \frac{\mu A}{MHz \times LE}$$

The parameters in this equation are shown below: